

Amendments to the Claims:

64. (Previously Presented): A method of forming a trench isolation region comprising:

forming an isolation trench within semiconductive material of a semiconductive substrate; and

filling the isolation trench with electrically insulative material, the filling comprising an initially liquid deposition within the isolation trench, the filling comprising a subsequent initially solid deposition within the isolation trench.

65. (Previously Presented): The method of claim 64 wherein the filling comprises forming an oxide layer over sidewalls of the trench prior to both of the initially liquid deposition and the subsequent initially solid deposition.

66. (Previously Presented): The method of claim 64 wherein the liquid comprises a silanol.

67. (Previously Presented): The method of claim 64 wherein the insulative material comprises silicon dioxide.

68. (Previously Presented): The method of claim 64 wherein the liquid deposition lowers an aspect ratio of the trench from what is was prior to the liquid deposition.

Claims 69-106 (Canceled).

107. (New): The method of claim 64 comprising solidifying material of the initially liquid deposition prior to the subsequent initially solid deposition.

108. (New): The method of claim 64 wherein the initially liquid deposition and the initially solid deposition occur at different temperatures.

109. (New): The method of claim 108 wherein the initially liquid deposition is conducted at temperature lower than that of the initially solid deposition.

110. (New): The method of claim 64 comprising annealing the material of the initially liquid deposition prior to the subsequent initially solid deposition.

111. (New): The method of claim 110 wherein the annealing is effective to solidify the material of the initially liquid deposition prior to the subsequent initially solid deposition.

112. (New): The method of claim 64 wherein the initially liquid deposition comprises introducing SiH_4 and H_2O_2 into a chamber within which the semiconductive substrate is received.

113. (New): The method of claim 64 wherein the initially liquid deposition comprises introducing SiH_4 , H_2O_2 , and N_2 into a chamber within which the semiconductive substrate is received.

114. (New): The method of claim 64 wherein the initially liquid deposition comprises introducing $(\text{CH}_3)_z\text{SiH}_{4-z}$ and H_2O_2 into a chamber within which the semiconductive substrate is received, where z is at least 1 and no greater than 4.

115. (New): The method of claim 114 wherein the $(\text{CH}_3)_z\text{SiH}_{4-z}$ comprises CH_3SiH_3 .

116. (New): The method of claim 64 wherein material of the initially liquid deposition deposits over a base of the isolation trench faster than over sidewalls of the isolation trench.

117. (New): The method of claim 64 wherein material of the initially liquid deposition deposits over a base of the isolation trench thicker than over sidewalls of the isolation trench.

118. (New): The method of claim 64 comprising exposing material of the initially liquid deposition to ultraviolet light prior to the subsequent initially solid deposition.

119. (New): The method of claim 118 comprising exposing material of the initially liquid deposition to a temperature greater than a temperature at which the initially liquid deposition initially occurred prior to said exposing to ultraviolet light.

120. (New): The method of claim 64 comprising exposing material of the initially liquid deposition to an electron beam prior to the subsequent initially solid deposition.

121. (New): The method of claim 120 comprising exposing material of the initially liquid deposition to a temperature greater than a temperature at which the initially liquid deposition initially occurred prior to said exposing to the electron beam.

122. (New): The method of claim 64 comprising exposing material of the initially liquid deposition to a plasma prior to the subsequent initially solid deposition.

123. (New): The method of claim 122 comprising exposing material of the initially liquid deposition to a temperature greater than a temperature at which the initially liquid deposition initially occurred prior to said exposing to plasma.

124. (New): The method of claim 64 comprising exposing material of the initially liquid deposition to RF energy prior to the subsequent initially solid deposition.

125. (New): The method of claim 124 comprising exposing material of the initially liquid deposition to a temperature greater than a temperature at which the initially liquid deposition initially occurred prior to said exposing to RF energy.